

Appl No 10/710,548
Amdt. Dated 06/13/2007
Reply to Office action of April 13, 2007

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-8. (canceled)

9. (currently amended) Bipolar device, comprising:

a collector region,
a base film disposed atop the collector region;
an emitter structure formed atop the base layer; and
a stress film disposed adjacent the emitter structure and atop the base film;
wherein:
the emitter structure is "T-shaped", having a lateral portion atop an upright portion;
a bottom of the upright portion ~~forms a contact to~~ contacts the base film;
the lateral portion overhangs the base film;
the stress film comprises nitride; and
the stress film covers and is in direct contact with exposed surfaces of the emitter structure; and
the stress film covers and is atop and in direct contact with exposed surfaces of the base film.

10. (Original) The bipolar device of claim 9, wherein the stress film is disposed in close proximity to an intrinsic portion of the device.

11. (canceled)

12. (Original) The bipolar device of claim 9, wherein the stress film is a compressive film.

13. (Original) The bipolar device of claim 9, wherein the stress film is a tensile film.

14. (canceled)

15. (Original) The bipolar device of claim 9, wherein the stress film has at least 0.5 GPa intrinsic stress.

16. (previously presented) The bipolar device of claim 9, wherein the stress film comprises:
means for creating compressive strain in the device to increase mobility of electrons in the device; and
means for creating tensile strain in the device to increase mobility of holes in the device.

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17. (previously presented) The bipolar device of claim 16, wherein the compressive and tensile strain are located in close proximity to an intrinsic portion of the device.

18-20. (canceled)